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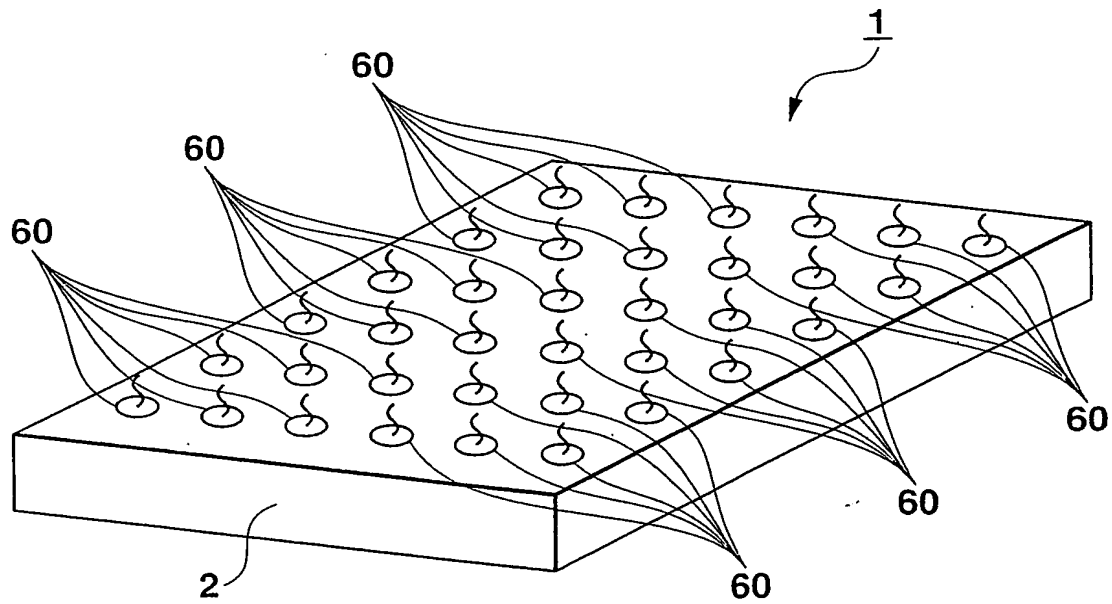


FIG.1

FIG.2

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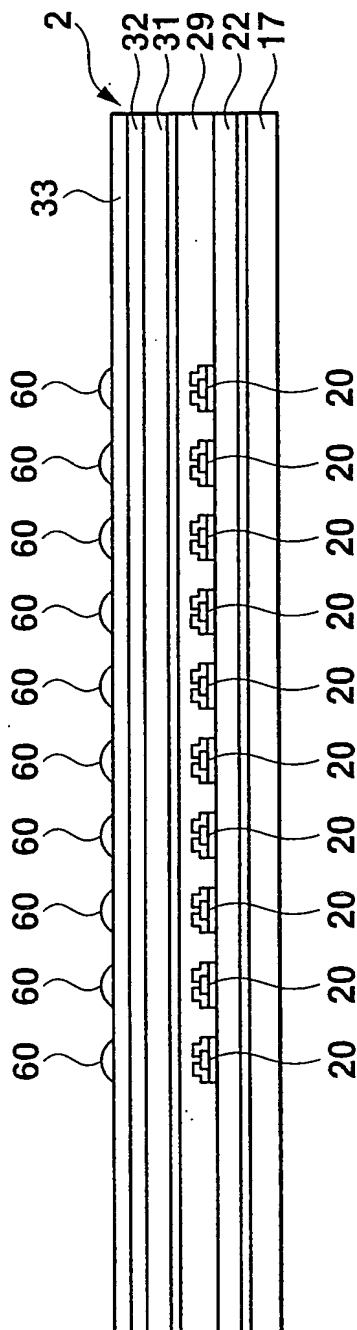


FIG.3

A detailed cross-sectional view of a semiconductor device 60. The device consists of a substrate 17 with multiple layers: 21, 22, 23, 24, 25, 26, 27, 28, 29, 30, 31, 32, and 33. A central region contains a structure with a central block 25 and side blocks 24 and 26. A top layer 61 is shown with wavy lines, and a top surface 60 is indicated by an arrow. A side surface 20 is also indicated by an arrow.

FIG.4B

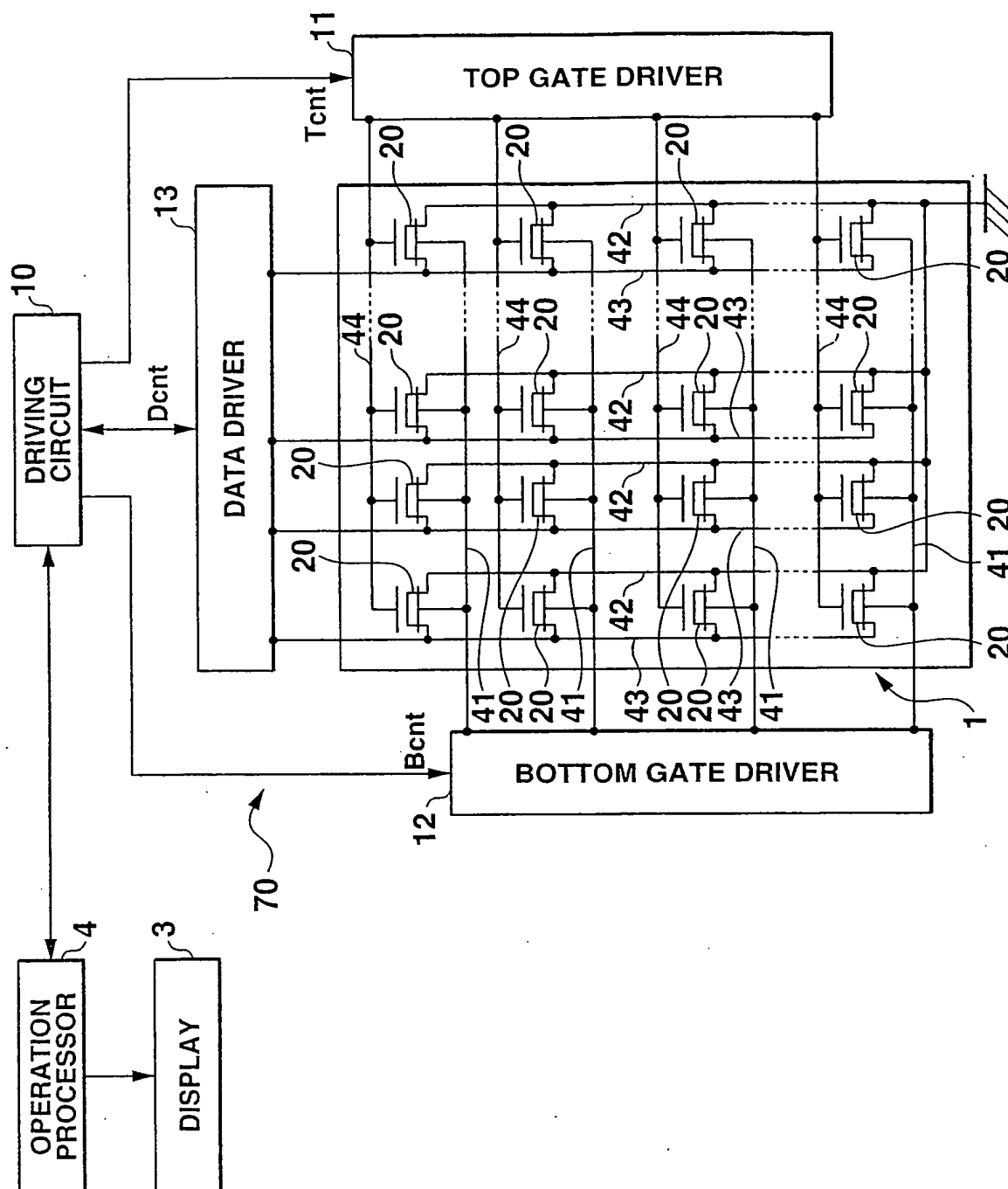


FIG. 5

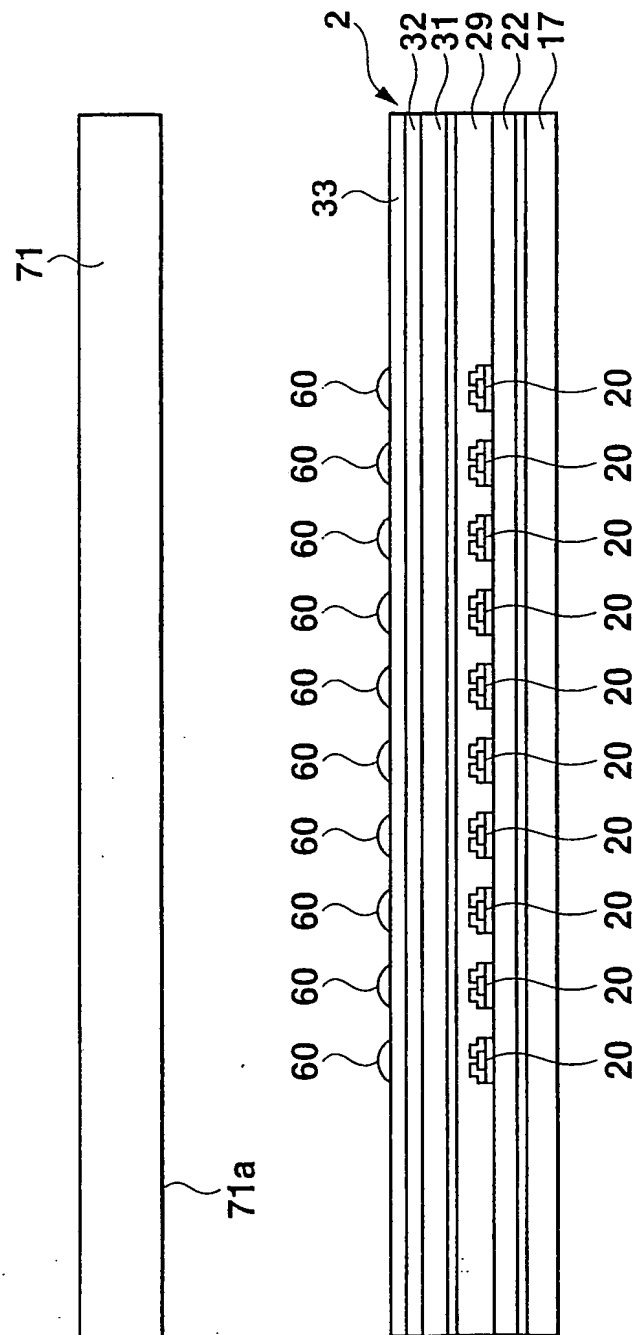


FIG. 6

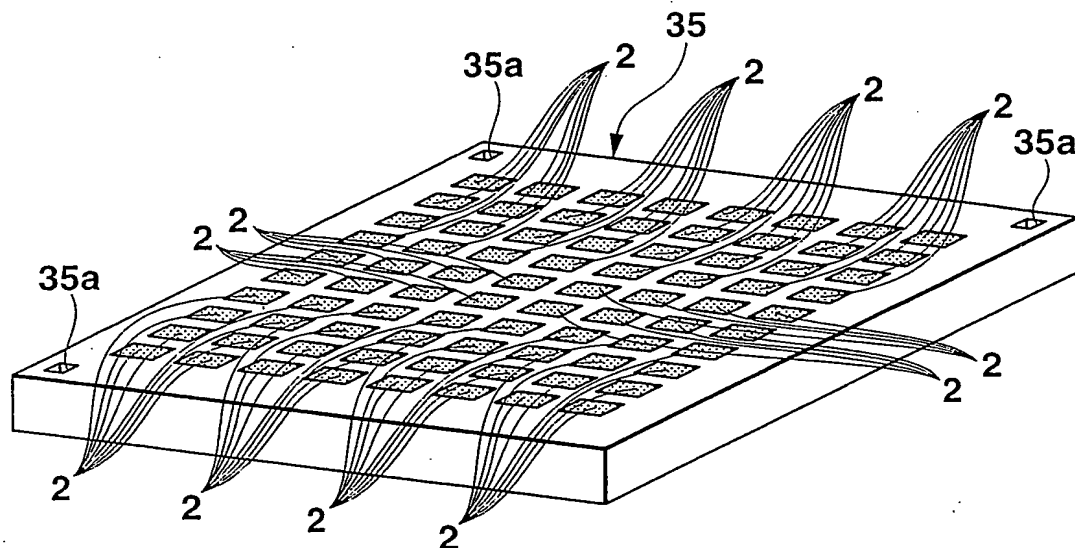


FIG.7

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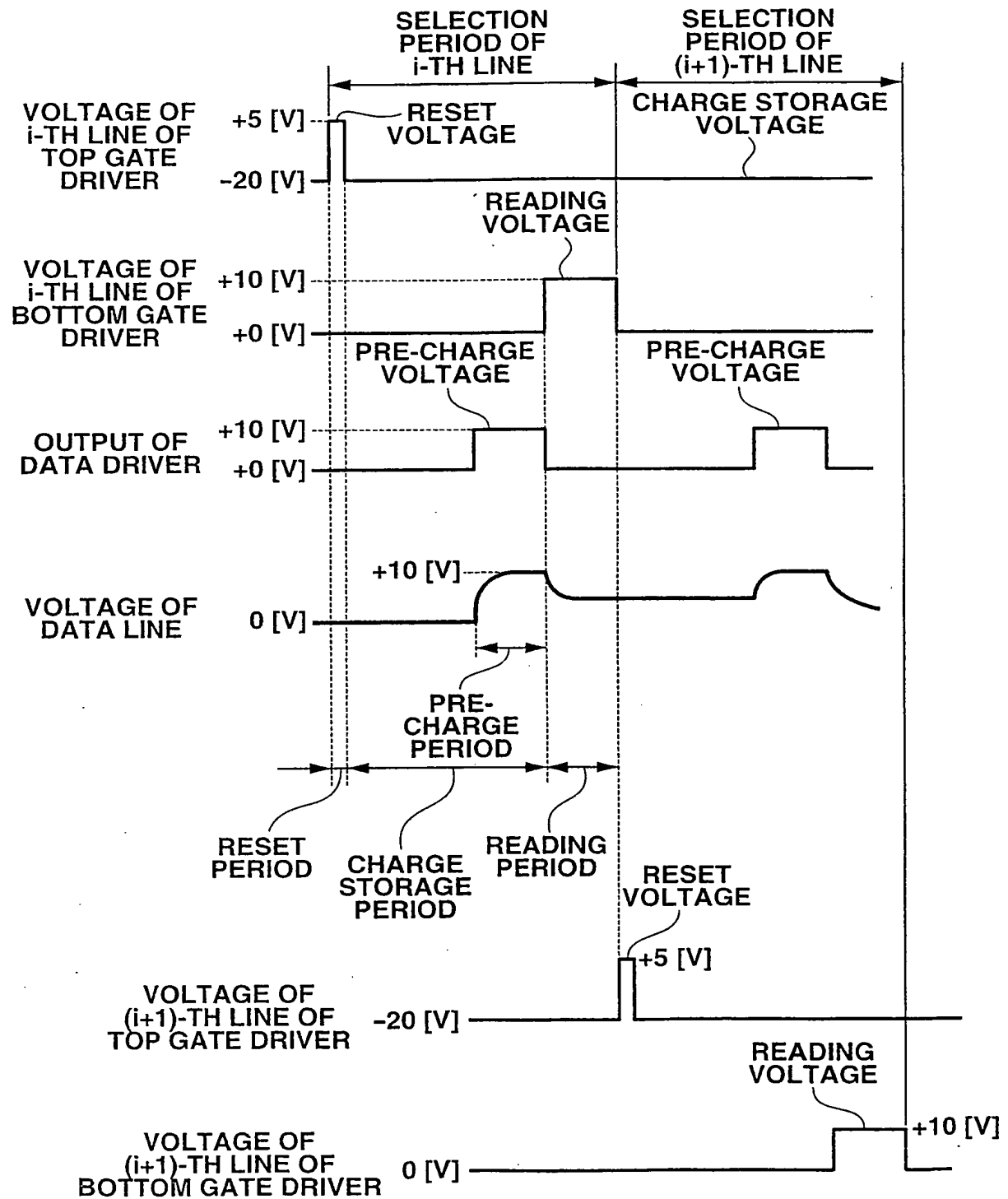


FIG.8

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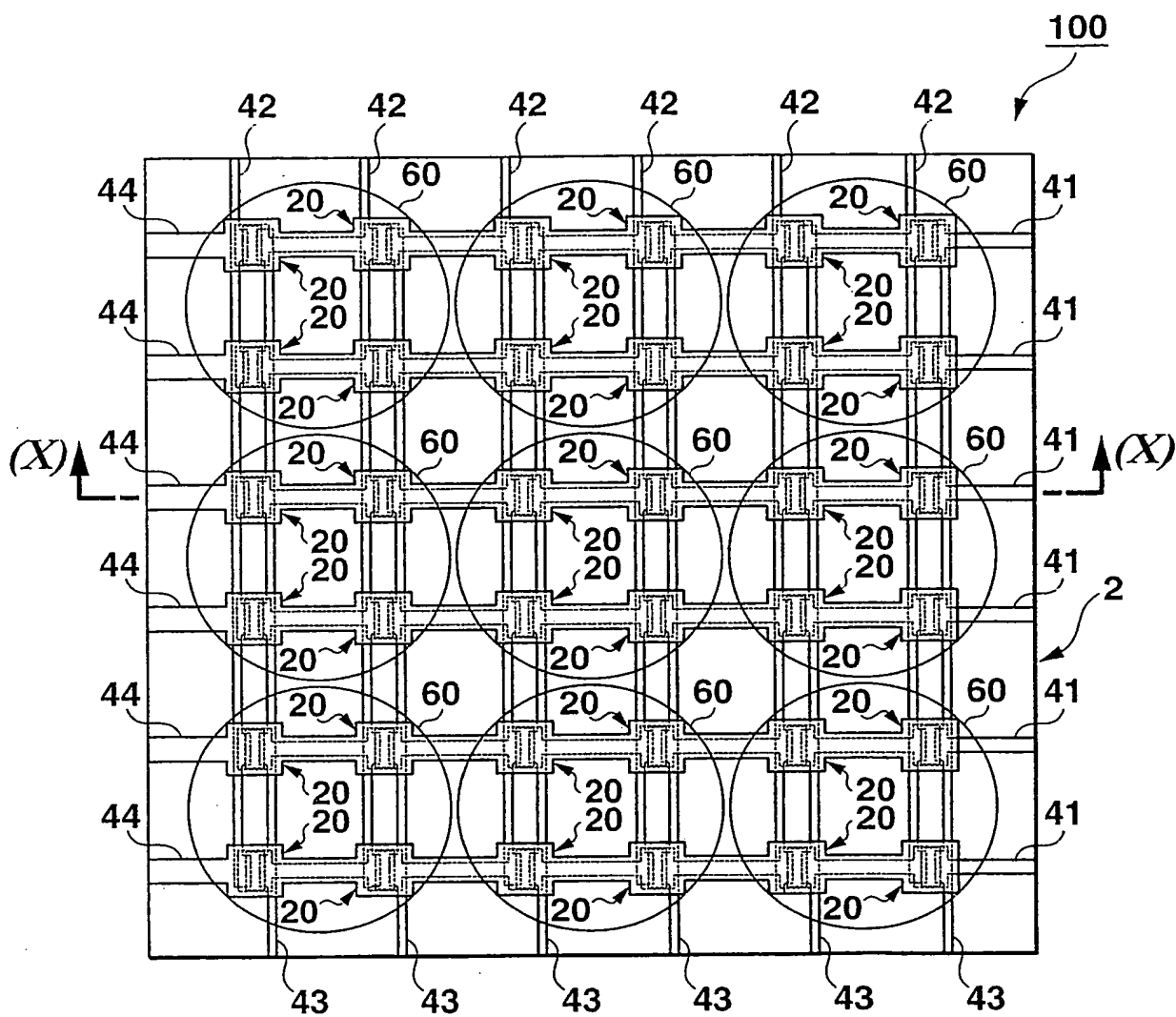


FIG.9

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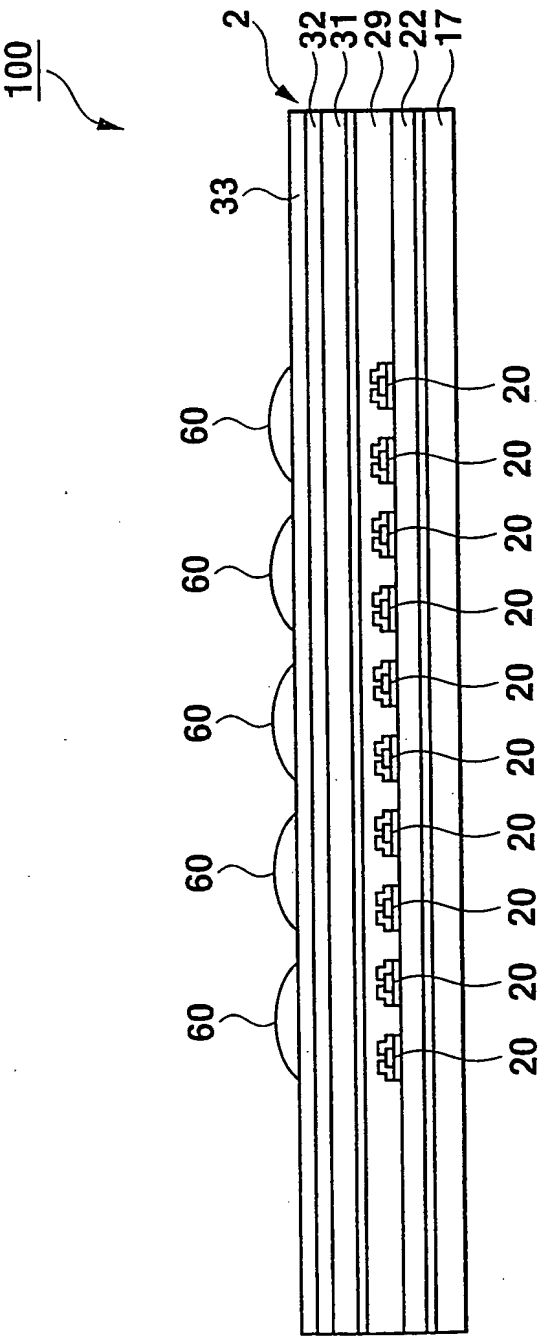


FIG.10

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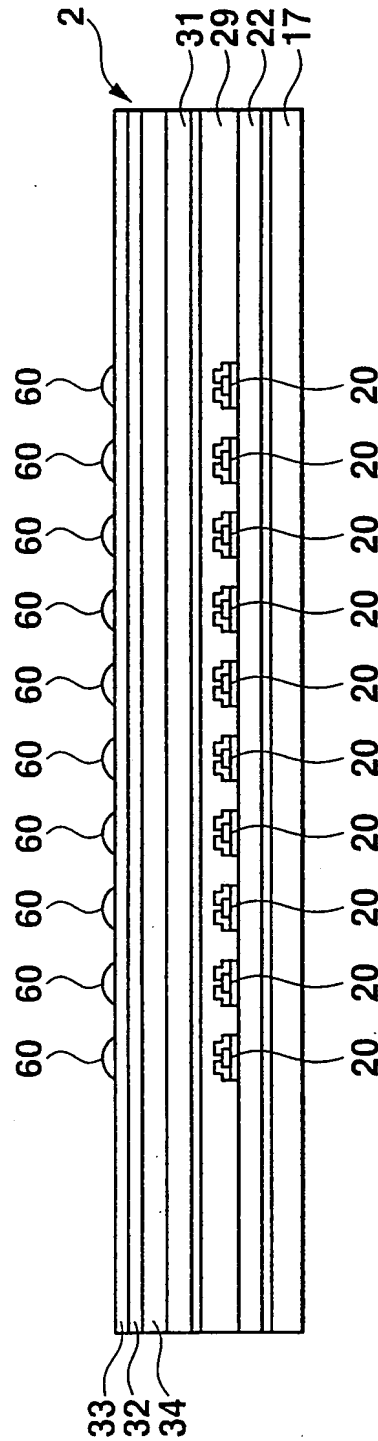


FIG.11

FIG.12B

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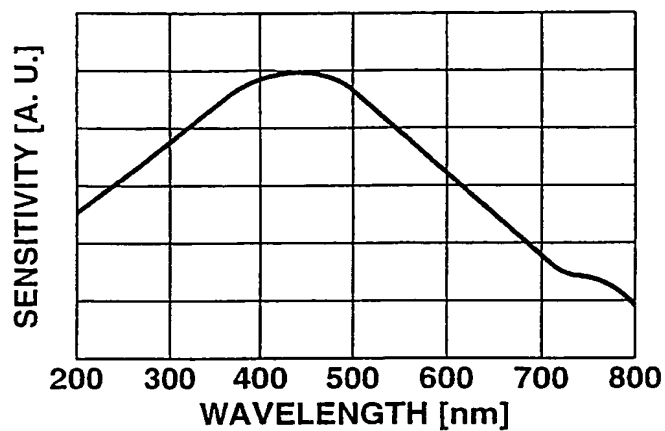


FIG. 13A

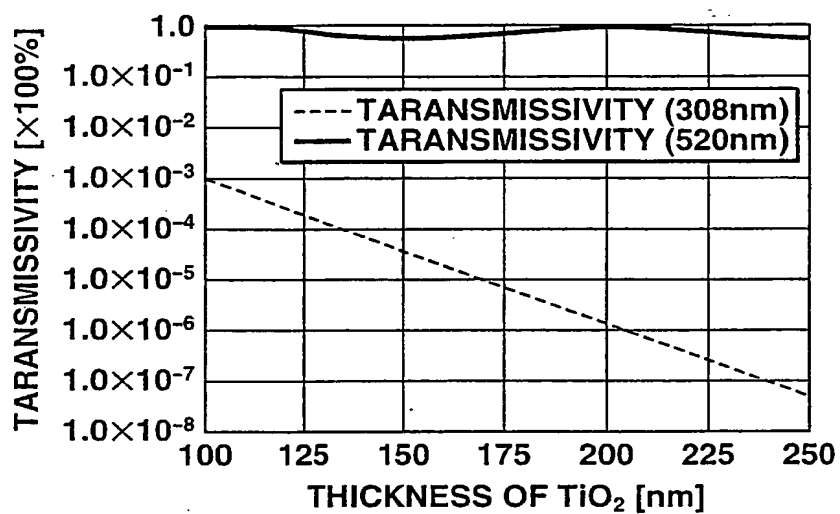


FIG. 13B

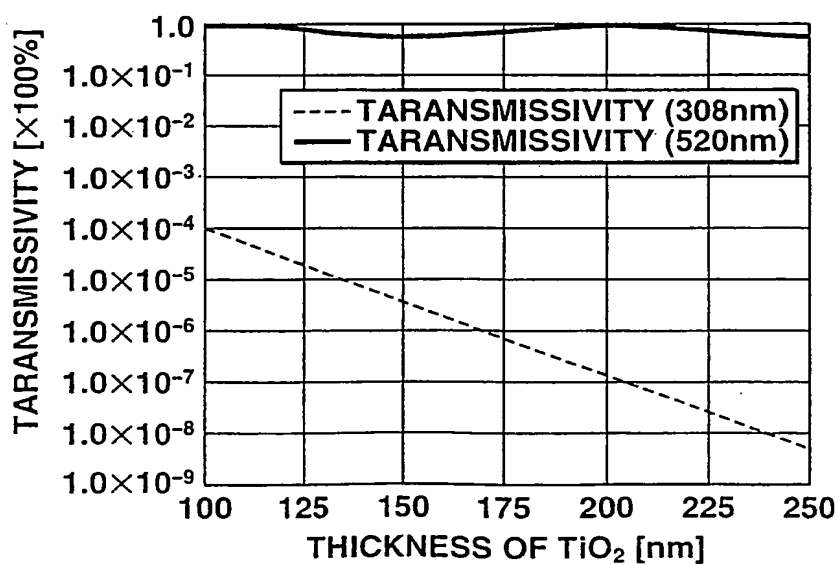


FIG. 13C

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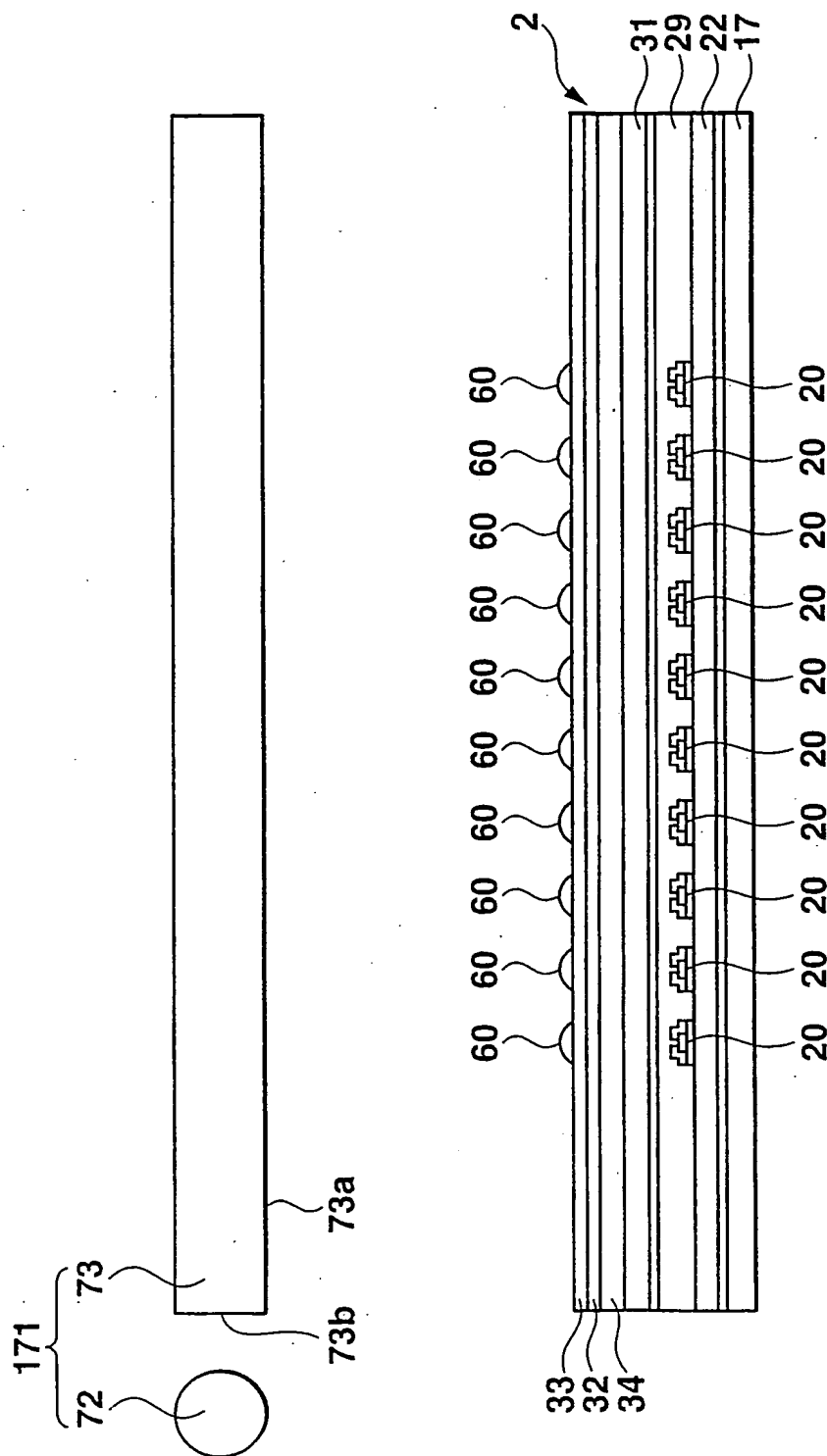


FIG.14

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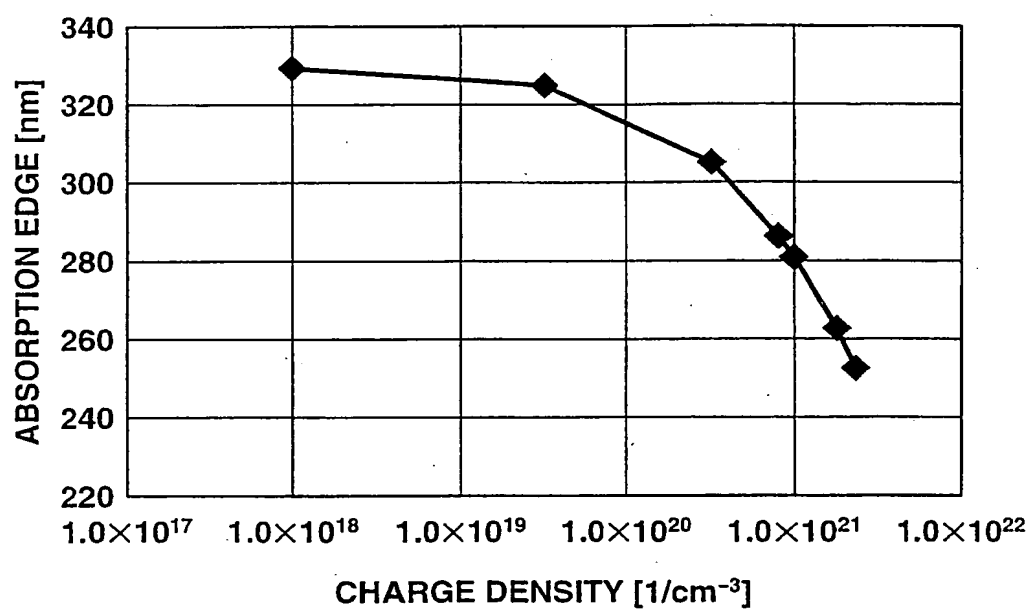


FIG.15

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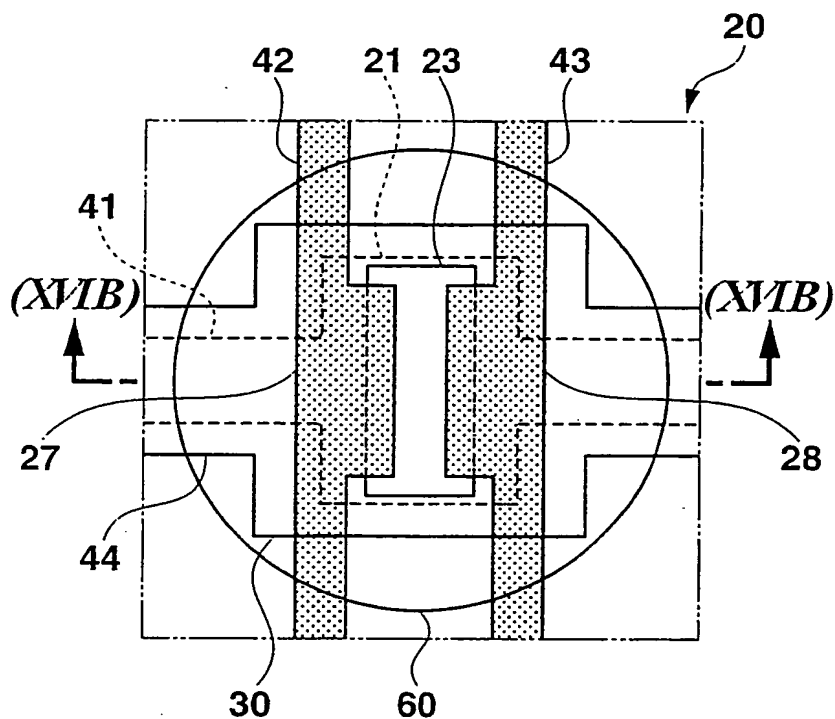


FIG. 16A

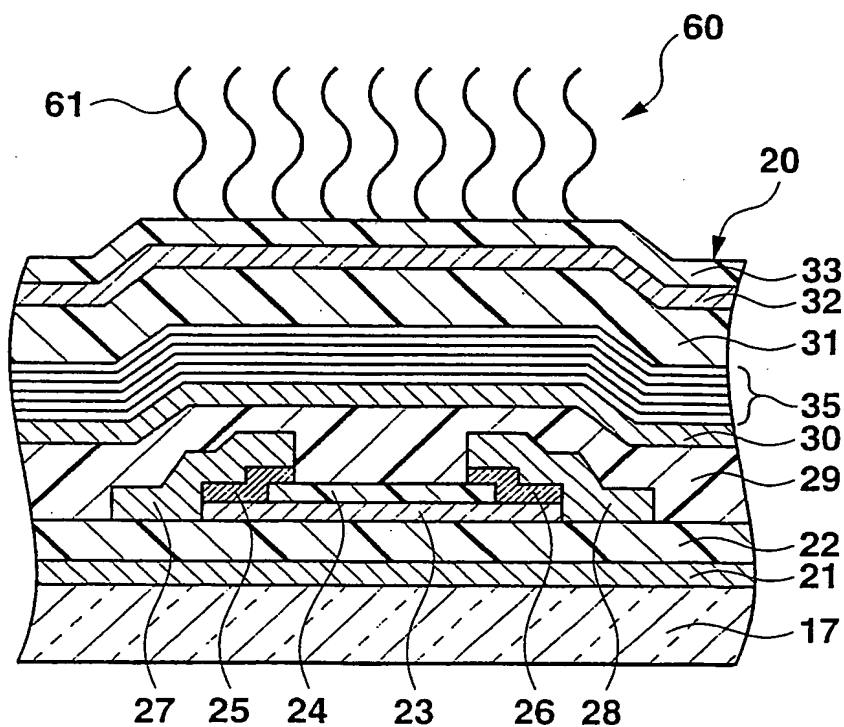


FIG. 16B

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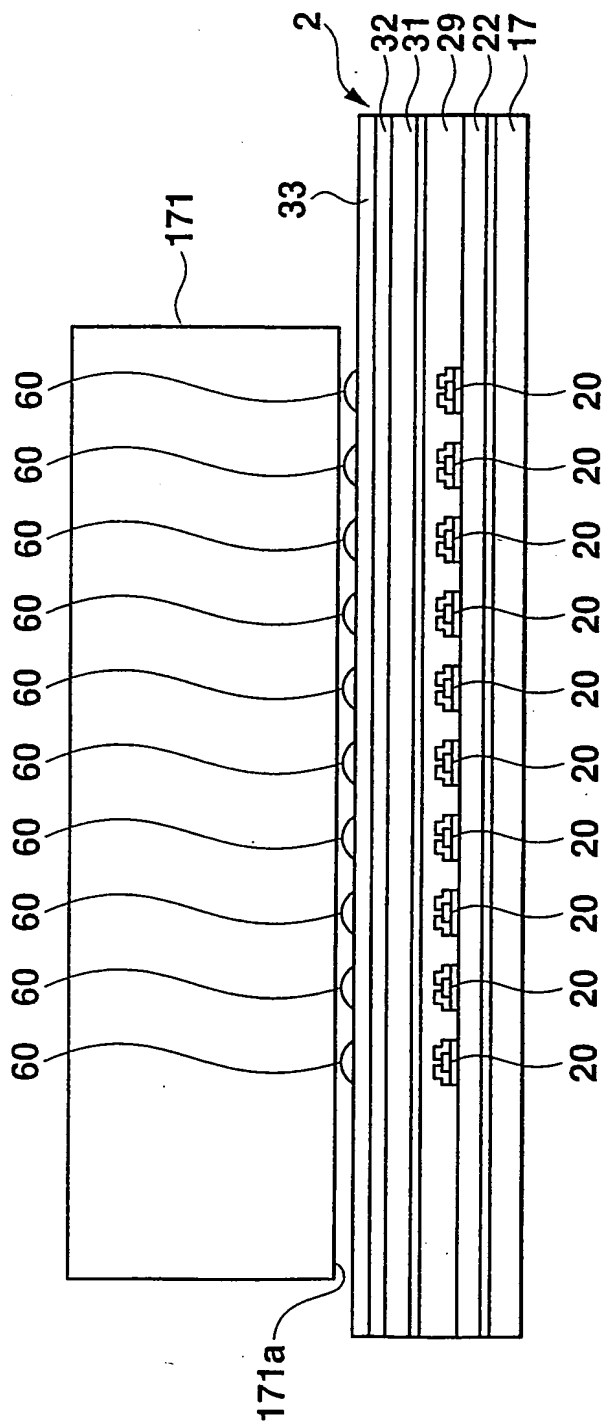


FIG.17

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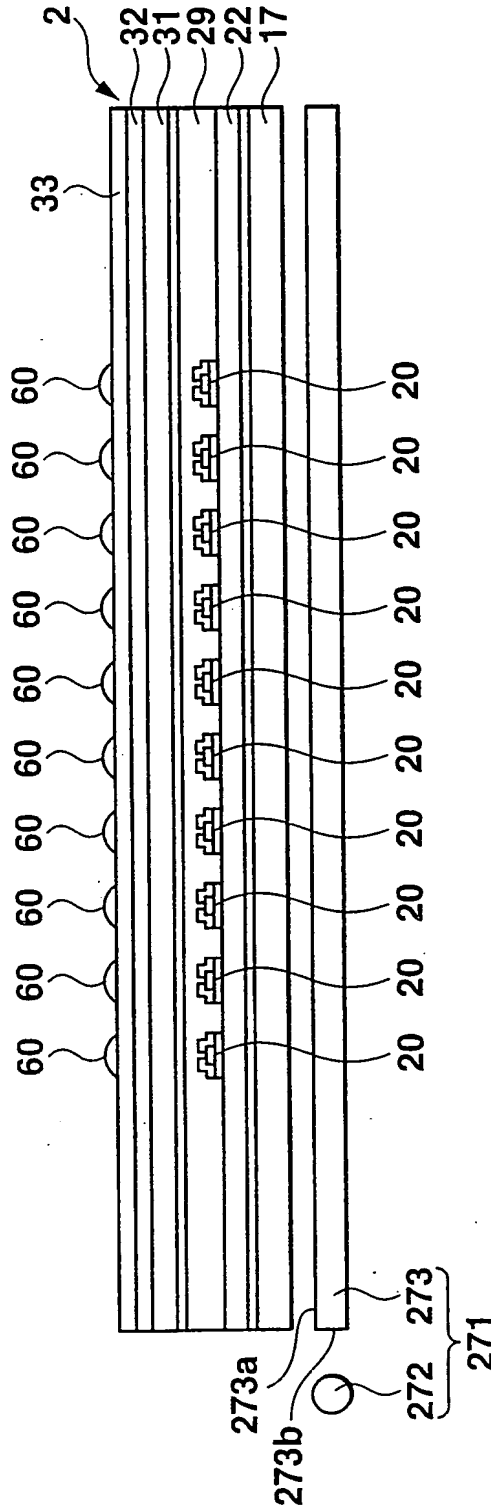


FIG.18